

**Silicon PNP Power Transistors**

**2SB434**

**DESCRIPTION**

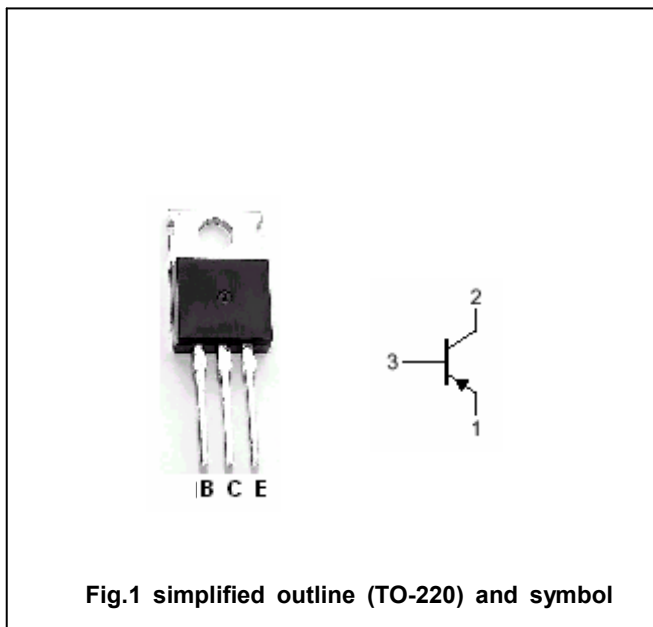
- With TO-220 package
- Complement to type 2SD234

**APPLICATIONS**

- For low frequency power amplifier and switching applications

**PINNING**

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



**Absolute maximum ratings(Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-60	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-50	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-6	V
I <sub>C</sub>	Collector current		-3	A
P <sub>C</sub>	Collector power dissipation		1.5	W
		T <sub>C</sub> =25°C	25	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## 2SB434

## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-5mA, I <sub>B</sub> =0	-50			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-1mA, I <sub>E</sub> =0	-60			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-1mA, I <sub>C</sub> =0	-6			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-3A; I <sub>B</sub> =-0.3A			-1.2	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-3A; I <sub>B</sub> =-0.3A			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-40V; I <sub>E</sub> =0			-10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-4V; I <sub>C</sub> =0			-10	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-0.5A; V <sub>CE</sub> =-1V	40		240	
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =-10V, f=1MHz		90		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.5A; V <sub>CE</sub> =-10V		3		MHz

◆ h<sub>FE</sub> Classifications

R	O	Y
40-80	70-140	120-240

